IN THE CLAIMS:

1-6. (Cancelled).

7. (Original) A semiconductor manufacturing method which performs reactive gas processing, wherein, when a substrate carrying system inserts a substrate from an airtight space in the substrate carrying system into a reaction chamber, and when said substrate is ejected from said reaction chamber to said airtight space, reactive gas is fed into said reaction chamber and reacts therein, the method comprising:

a substrate carrying step of measuring the moisture content in said airtight space by means of a first moisture measuring device which is connected to said airtight space, and thereafter, inserting and ejecting said substrate by means of said substrate carrying system; and

a gas processing step of performing said reactive gas processing while measuring the moisture content in said reaction chamber by means of a second moisture measuring device, which is connected to said reaction chamber, after said substrate carrying step.

8. (Original) The semiconductor manufacturing method according to claim 7, said substrate carrying step comprising inserting said substrate from said airtight space to said reaction chamber or ejecting said substrate from said reaction chamber to said airtight space, after it has been confirmed that the moisture content in said airtight space is lower than a first default value; and

said gas processing step being a step in which said reactive gas processing is commenced after it has been confirmed that the moisture content in said reaction chamber is lower than a second default value.

9. (Original) The semiconductor manufacturing method according to claim 8, at least said second default value being lower than 1 ppm.

10. (Original) The semiconductor manufacturing method according to claim 7, at least one of said first moisture measuring device and said second moisture measuring device comprising a laser moisture measuring device which radiates laser light into a tubular cell main body, connected to said airtight space and said reaction chamber, and measures an absorption spectrum of transmitted laser light.

11-15. (Cancelled).